

# **BTA410Y-800BT**

3Q Hi-Com Triac Rev. 1 — 12 March 2012

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78D (TO-220) internally insulated plastic package. This "series BT" triac will commutate the full RMS current at the maximum rated junction temperature ( $T_{j(max)} = 150$  °C) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

### 1.2 Features and benefits

- 3Q technology for improved noise immunity
- High blocking voltage capability
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction operating temperature capability
- Internally insulated package

### **1.3 Applications**

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)

- Internally isolated mounting base
- Isolation voltage capability of 2500 V RMS
- Least sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Motor controls e.g. vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage	9	-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	100	А
Tj	junction temperature		-	-	150	°C
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 120 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	10	A



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I <sub>GT</sub> gate trigger current		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; see <u>Figure 7</u>	2	-	50	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; see <u>Figure 7</u>	2	-	50	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; see <u>Figure 7</u>	2	-	50	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM} = 536 \text{ V}; \text{ T}_{\text{j}} = 150 \text{ °C}; (V_{DM} = 67\% \text{ of } V_{DRM});$ exponential waveform; gate open circuit	1000	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 150 \text{ °C}; I_{T(RMS)} = 10 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu s;$ (snubberless condition); gate open circuit	20	-	-	A/ms

# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		<b>N</b> 1
2	T2	main terminal 2	mb	T2-T1
3	G	gate		`G sym051
mb	n.c.	mounting base; isolated		

### SOT78D (TO-220AB)

# 3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BTA410Y-800BT	TO-220AB	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220	SOT78D		

**BTA410Y-800BT** 

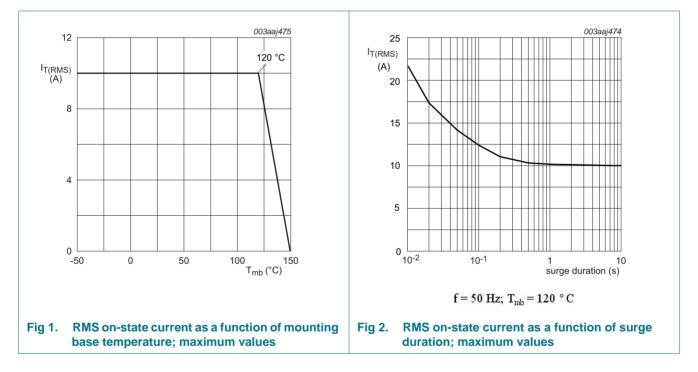
**3Q Hi-Com Triac** 

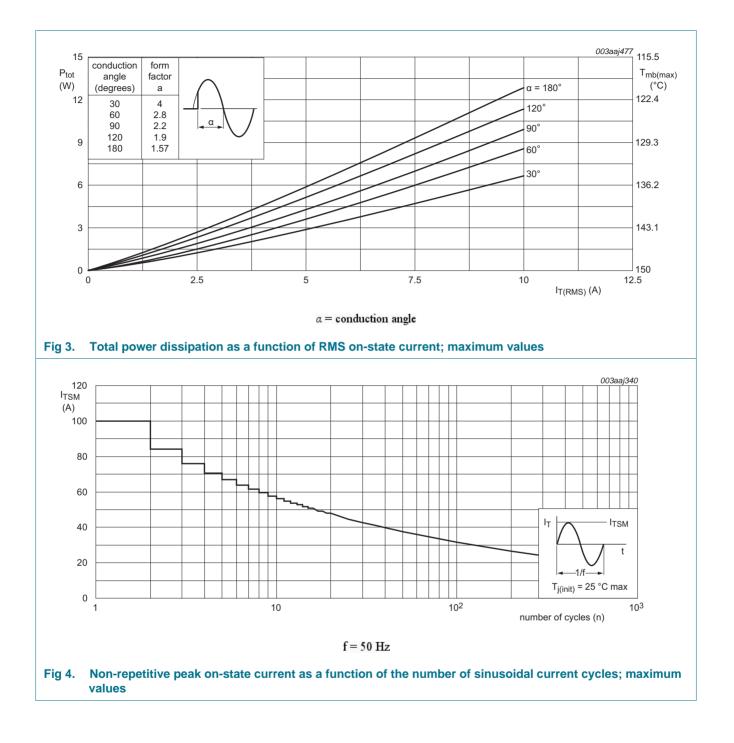
## 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

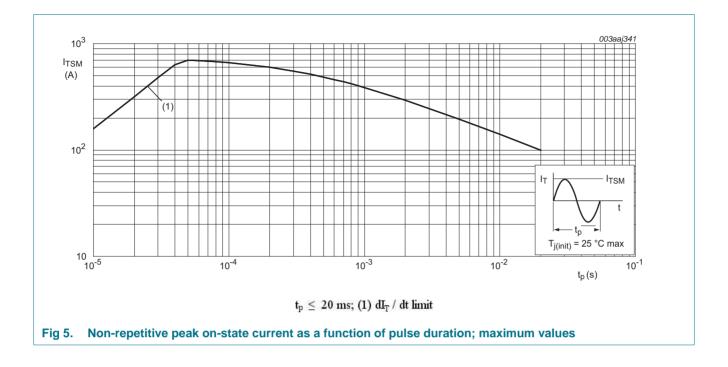
Symbol	Parameter	Conditions	Min	Max	Unit
Symbol	Falametei	Conditions	14(11)	INICX	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 120$ °C; see Figure 1; see Figure 2; see Figure 3	-	10	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	100	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	110	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	50	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu s$	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>i</sub>	junction temperature		-	150	°C





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## 5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	full cycle; see <u>Figure 6</u>	-	-	2.3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

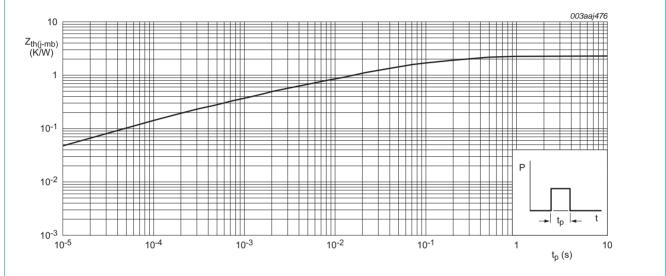


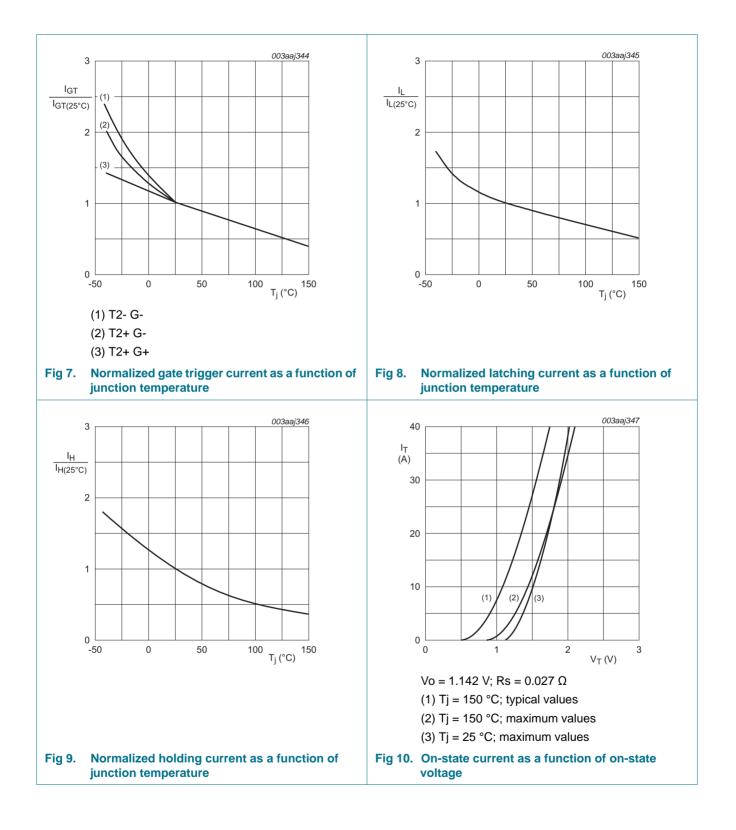
Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

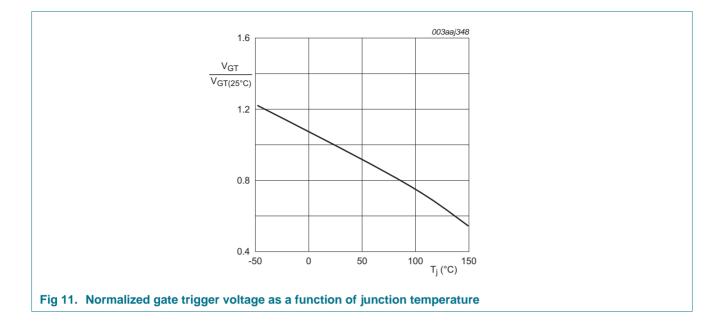
## 6. Isolation characteristics

Table 6.	Isolation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free ; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; T <sub>mb</sub> = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink ; $f = 1 \text{ MHz}$ ; $T_{mb} = 25 ^{\circ}\text{C}$	-	10	-	pF

## 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G+}; \text{ T}_j = 25 \text{ °C};$ see Figure 7	2	-	50	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 7	2	-	50	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 7	2	-	50	mA
IL	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; see <u>Figure 8</u>	-	-	60	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 8	-	-	90	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 8	-	-	60	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; see <u>Figure 9</u>	-	-	60	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	-	0.8	1.5	V
		V <sub>D</sub> = 400 V; T <sub>j</sub> = 150 °C; see <u>Figure 11</u>	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 150 °C	-	0.4	2	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 150 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	1000	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D = 400 \text{ V}; \text{ T}_j = 150 \text{ °C}; \text{ I}_{T(RMS)} = 10 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu\text{s};  (snubberless condition); gate open circuit$	20	-	-	A/ms
		$V_D$ = 400 V; $T_j$ = 150 °C; $I_{T(RMS)}$ = 10 A; $dV_{com}/dt$ = 10 V/µs; gate open circuit	28	-	-	A/ms
		$V_D = 400 \text{ V}; \text{ T}_j = 150 \text{ °C}; \text{ I}_{T(RMS)} = 10 \text{ A};$ dV <sub>com</sub> /dt = 1 V/µs; gate open circuit	45	-	-	A/ms





## 8. Package outline

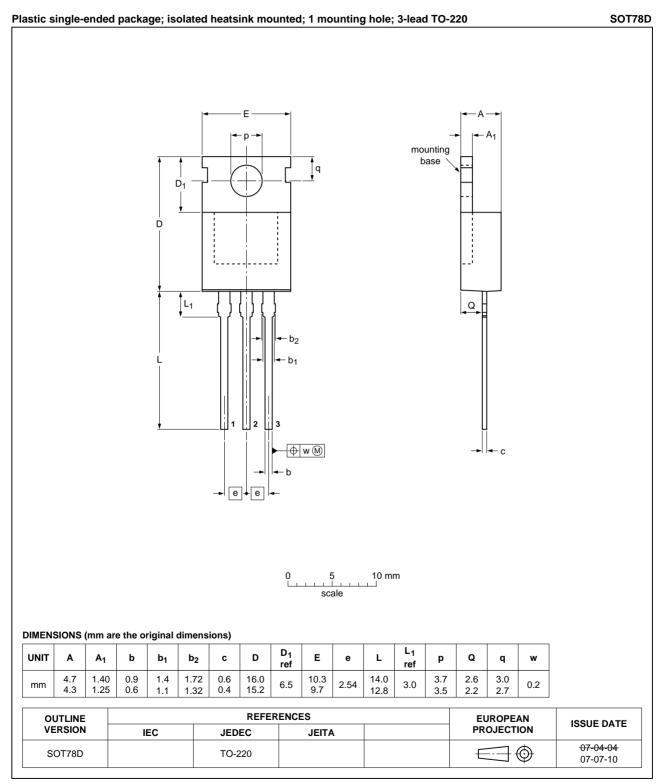


Fig 12. Package outline SOT78D (TO-220AB)

## 9. Revision history

Table 8. Revision h	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA410Y-800BT v.1	20120312	Product data sheet	-	-

## **10. Legal information**

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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